

Functional tests and selection of detectors for JEDI

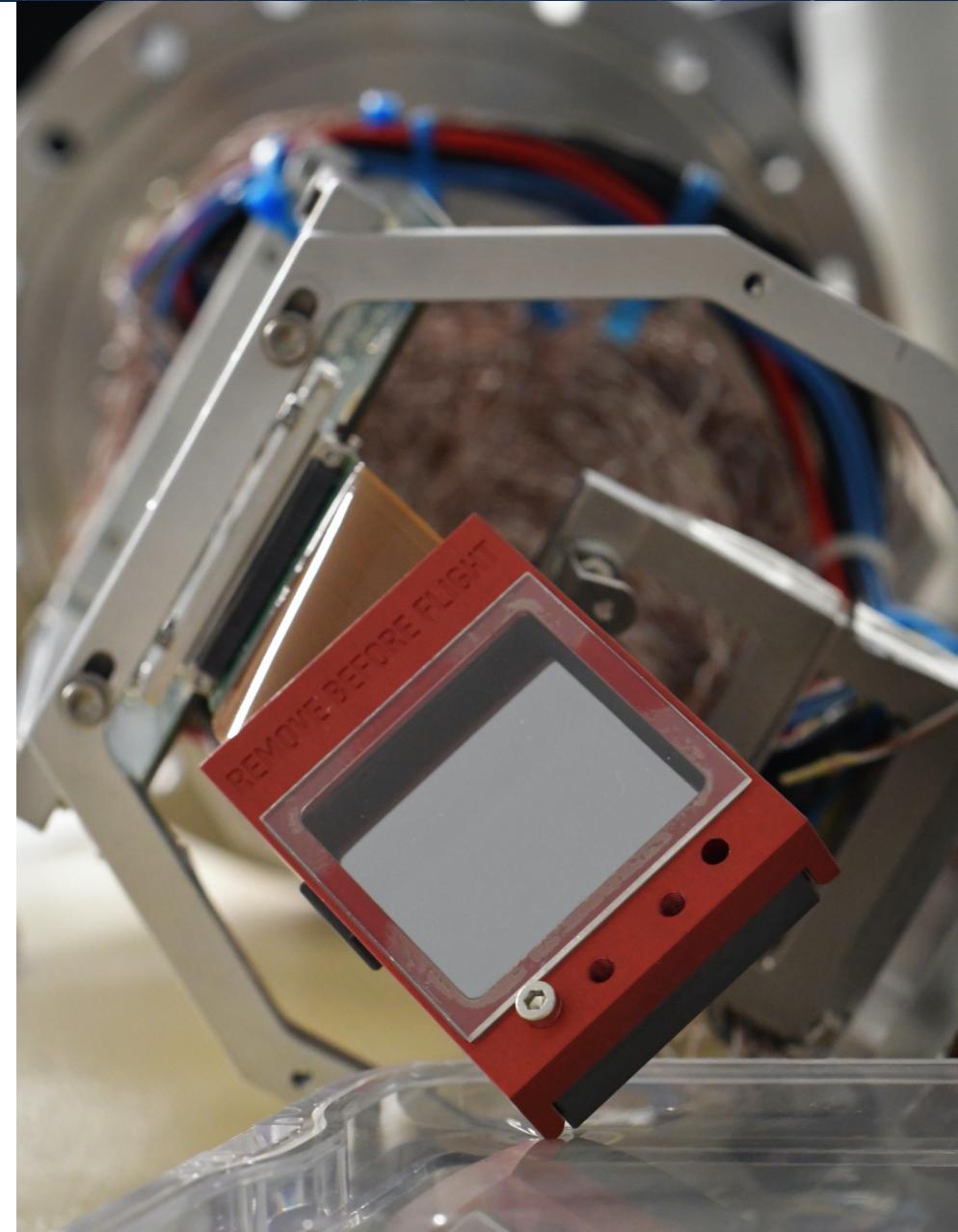
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together with ROB & CSL teams

Orsay, 5-6 May 2025

Main motivation

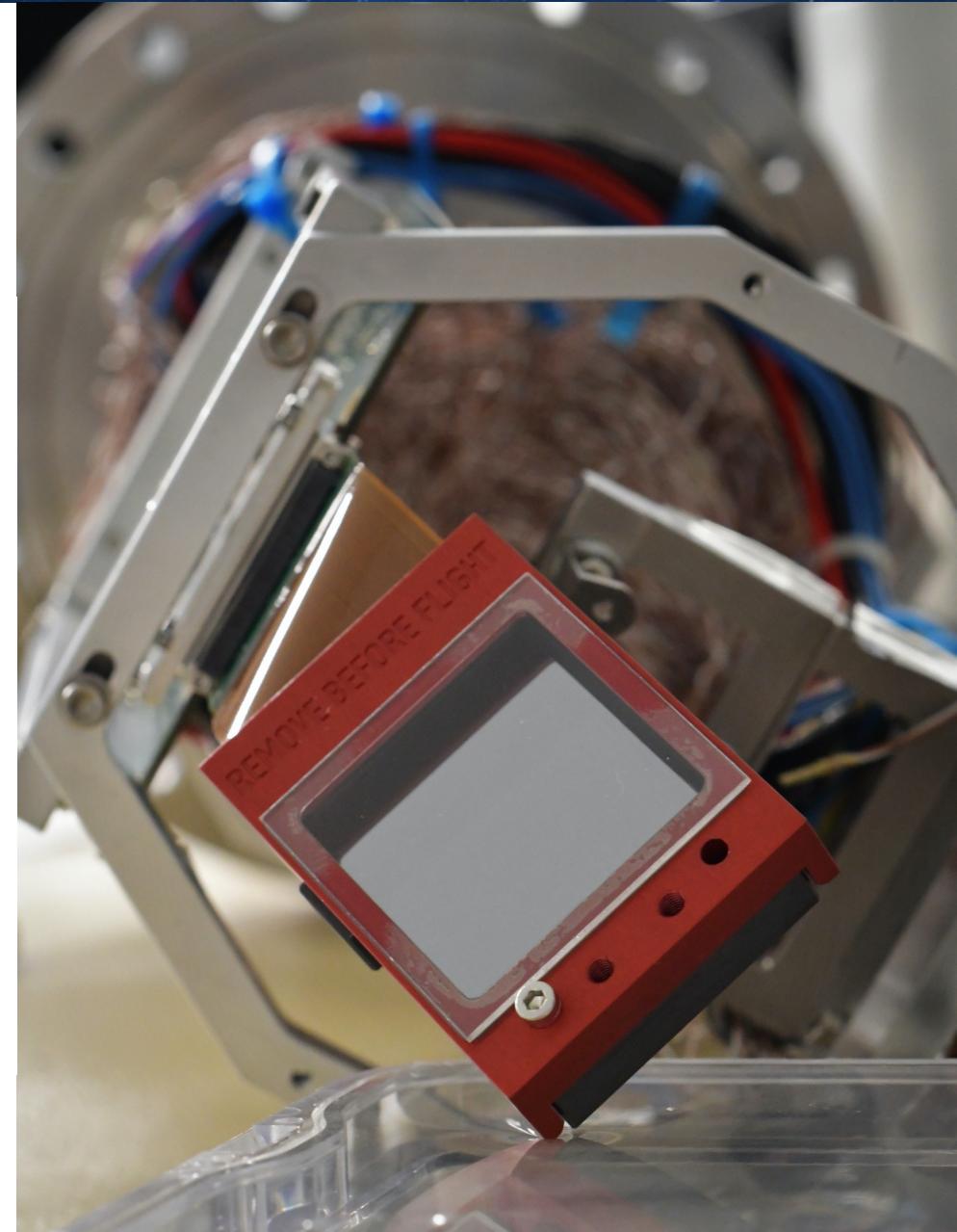
- To select the best “EUI” detector among ~10 available CMOS-BSI detectors* and provide basic characterization of its functionality.

* they are already stored in the CSL in a clean room (ISO 5) and ready for testing



Requirements comparison to heritage

Characteristic	EUI detector	PROJECT Requirement	Heritage Margin to PROJECT Req
Detector Format	3072 x 3072	3k x 3k	Complies
Pixel Pitch:	10 μm	10 μm	Complies
Full Well Charge:	> 80 ke (LG), > 5 ke (HG)	>80 ke (LG)	Complies
Dynamic Range:	> 84 dB (dual gain) @ -40°C		
Dark Current:	< 5 e/s/pix at -20°C	0.05 e/sec/pix at -50 °C (?)	
Readout Noise	< 5 e (HG) , < 50 e (LG)	2.8 e (HG) ?	
Radiation Hardness	100 krad	>50 krad	Complies
Operational Temp.	-60 / -40 °C	-60 / -40 °C	Complies
Output Read Rate:	13.6 Msps (1.5 fps 3kx3k)		



EUI BSI detectors will be submitted to the following tests:

1. Functional Test

(this is the first test that will be applied to all available detectors in order select the best ones for the further, more detailed tests)

- Dark current measurements taken at **different integration time** and at **ambient** temperature
 - Expected results:
 - Dark noise as a function of integration time
 - Number and type of defects (bright/dark pixels, rows etc)
 - Power consumption (**should be less than 1 watt of power**)

EUI BSI detectors will be submitted to the following tests:

2. Detector Performance Tests

(those are the tests that will be applied to the "short-listed" detectors in order select the best "flying" one)

- Noise evaluation (different integration time and different temperatures)
 - Bias
 - Dark current map
 - Stability assessment (dark and under illumination, very long integration time)
- Optical sensitivity evaluation (different integration time and different temperatures)
 - Non-Linearity (depends on the gain level) and Conversion Factor (**possible with the optical source**)
 - Flat-field measurements (**only with the EUV source**)

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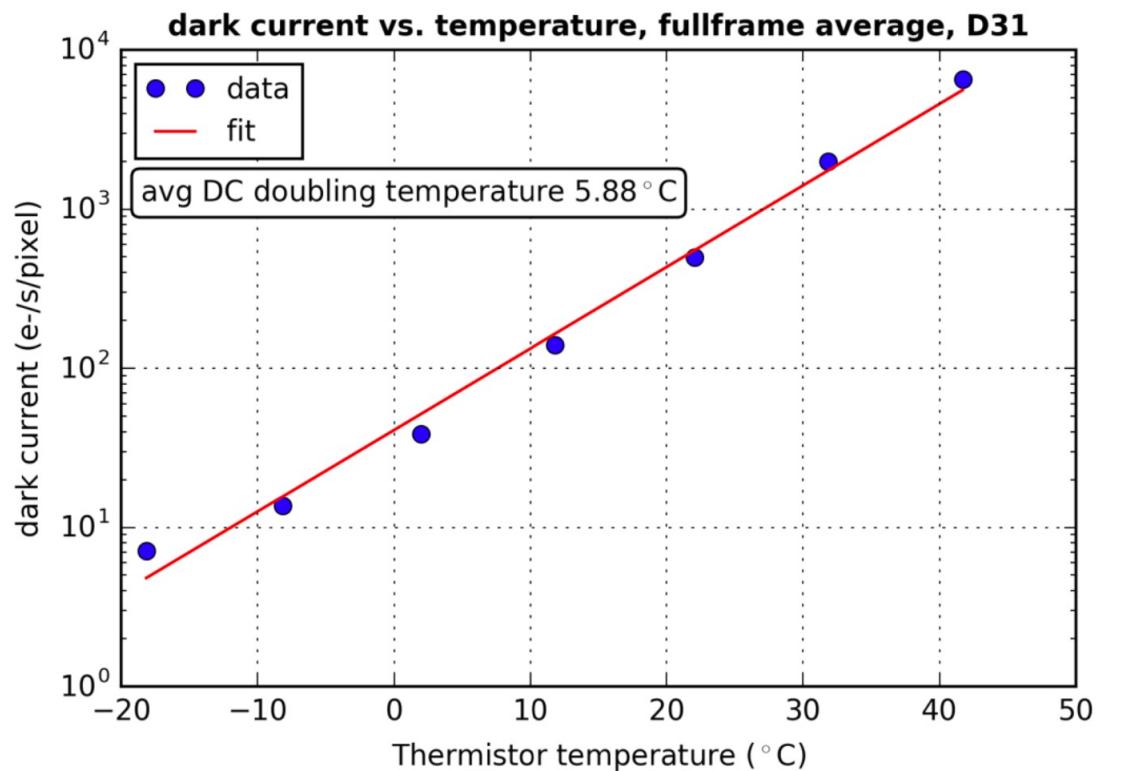


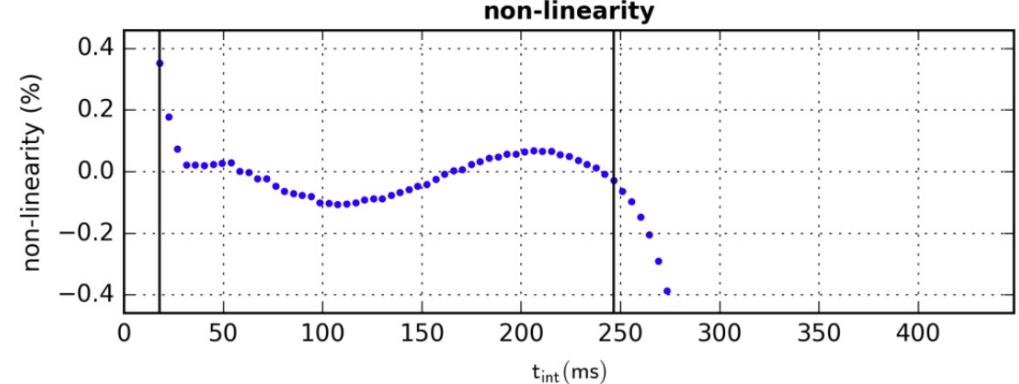
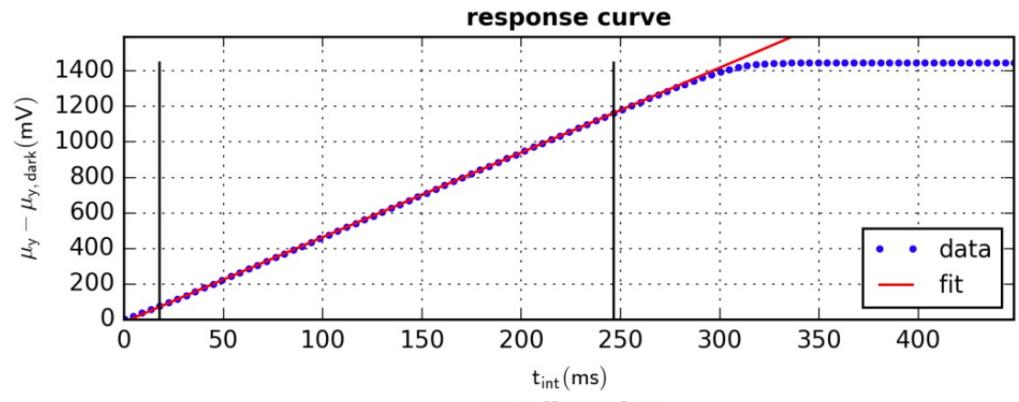
Figure 15: Dark current as function of temperature for BSI CoB D31.

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readout noise (*gain mode*) +



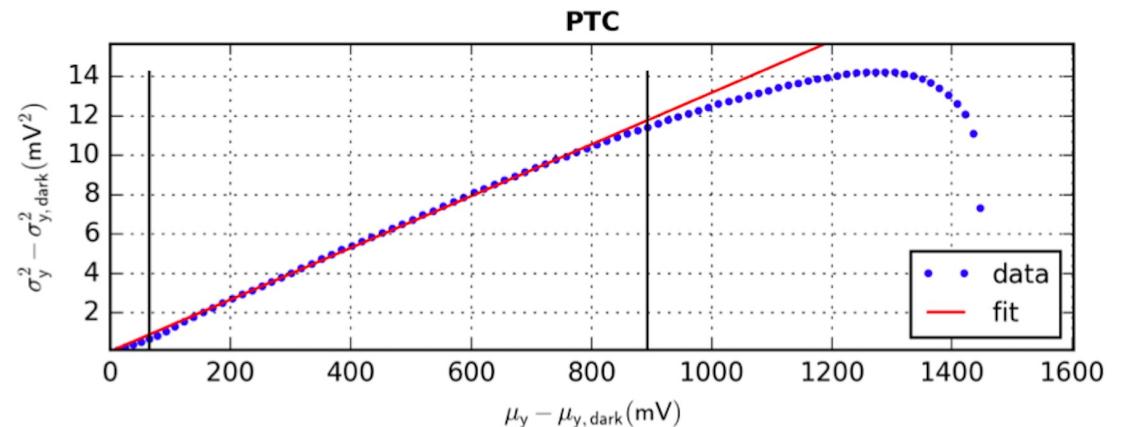
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the number of photoelectrons read out at the output of the chip (*integration time*)



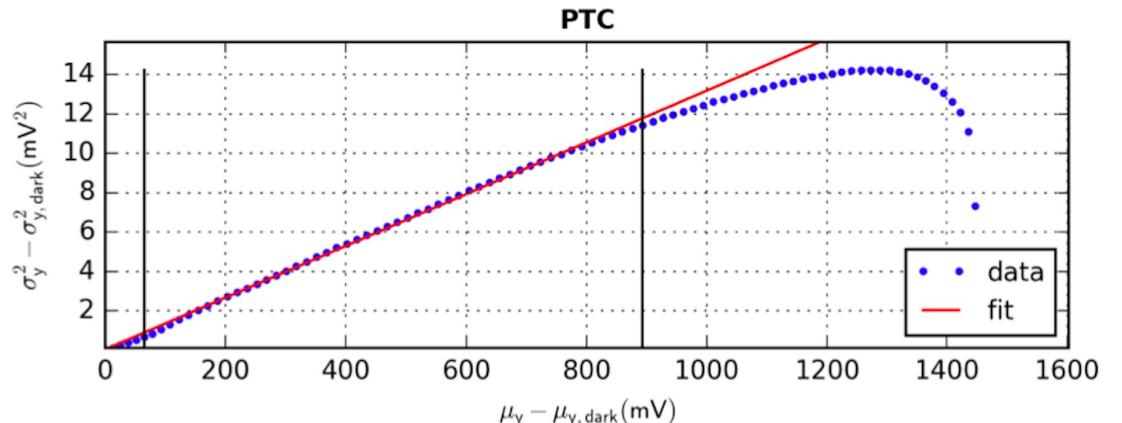
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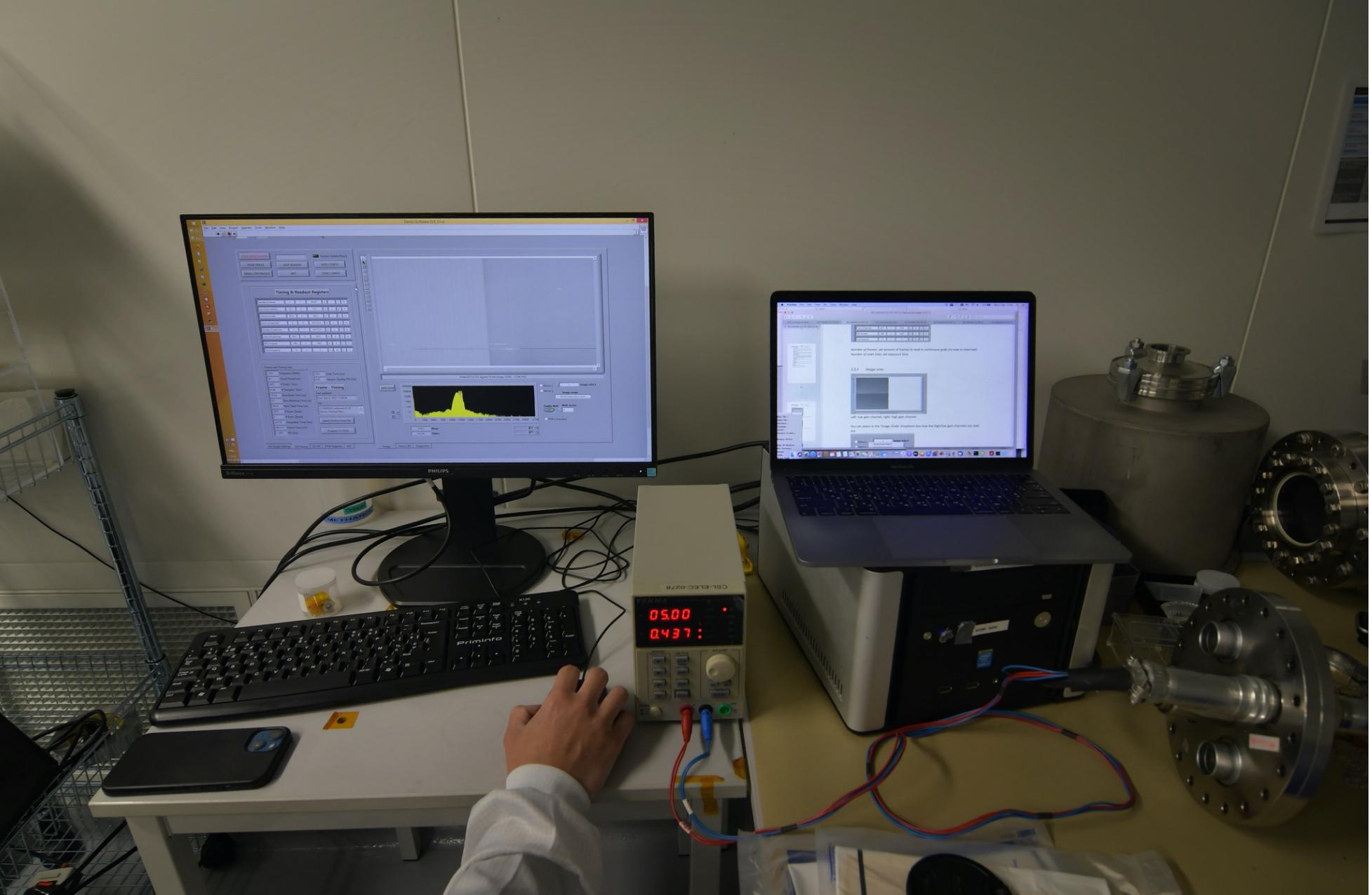


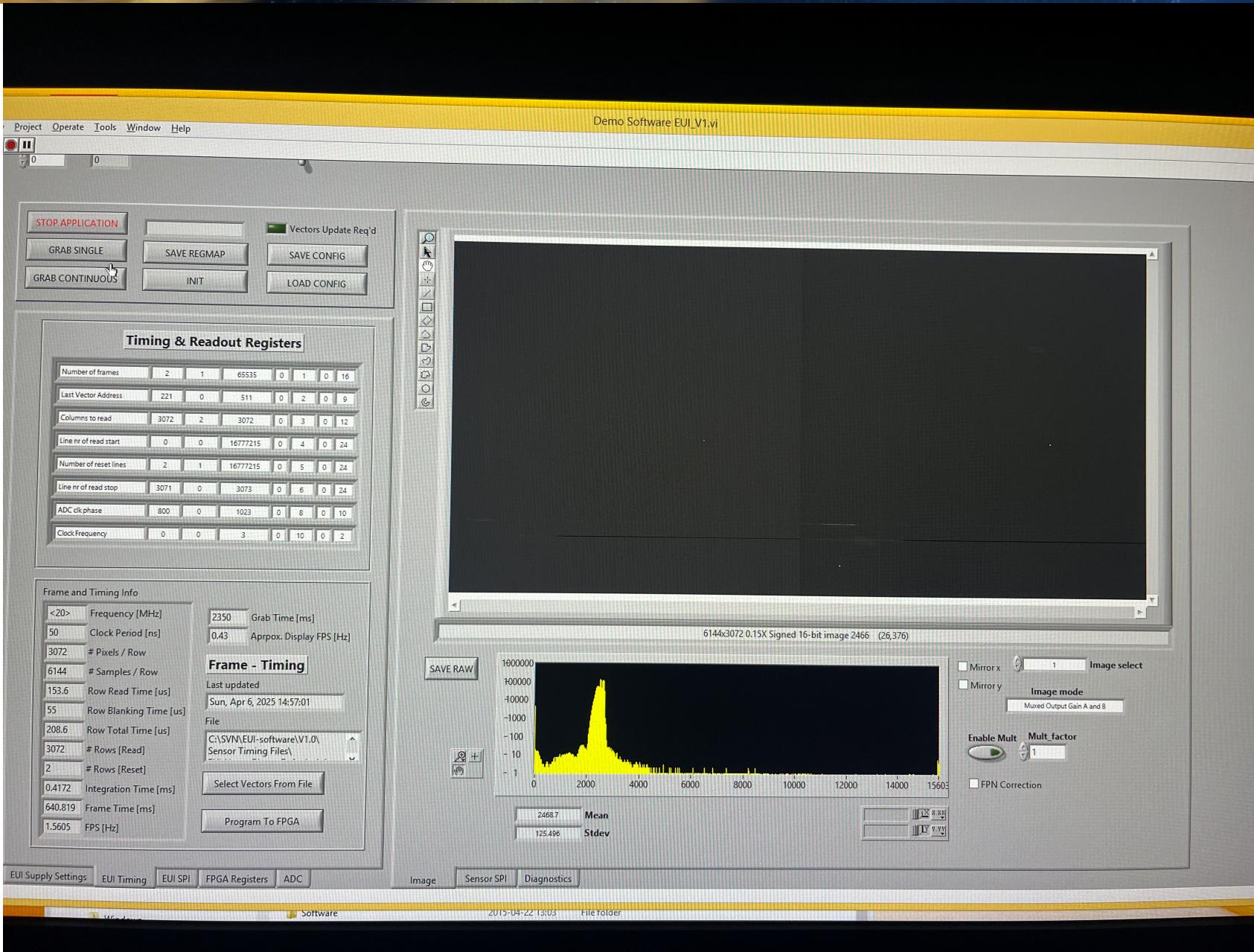
What we have learned from the previous missions (EUI, ASPIIICS):

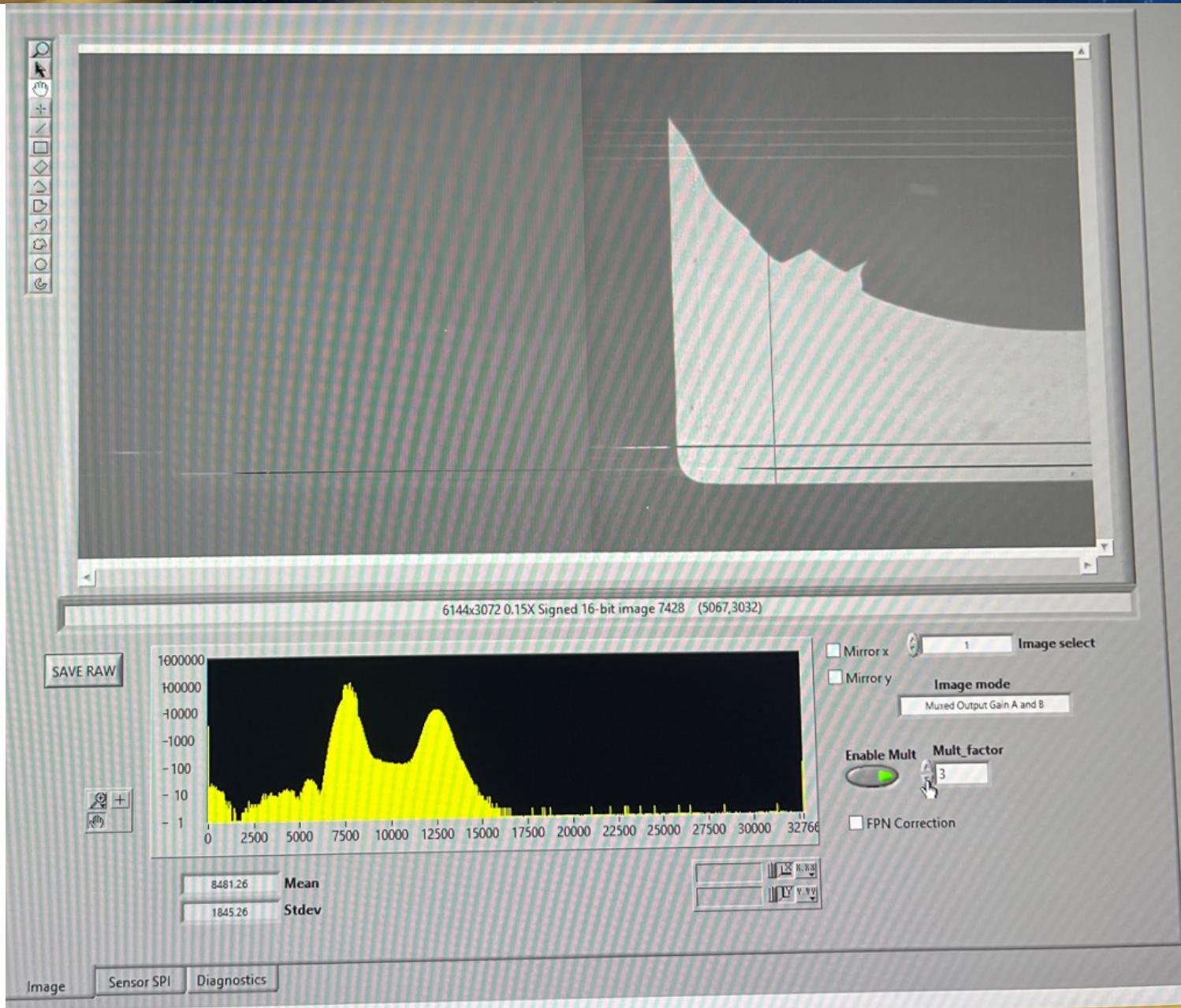
- bias is not constant
- significant non-linearity depending on the gain mode (we should not exceed the 2% threshold)

VIGIL
JEDI









We propose the next steps:

- To perform the functional tests for all available detectors at ambient temperature (ASAP);
- Depending on the number of short-listed detectors, put them in a vacuum chamber and perform different functional tests at various temperatures (check if the dark current measurements are in agreement with the previous “EUI” experiments);
- Perform the final flat-field measurements with the EUV source (Sergei’s calibration plan) for the best short-listed detectors.